

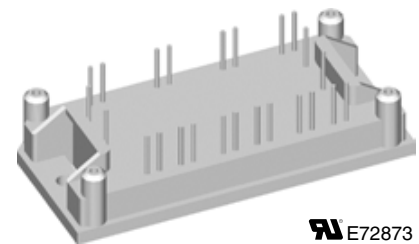
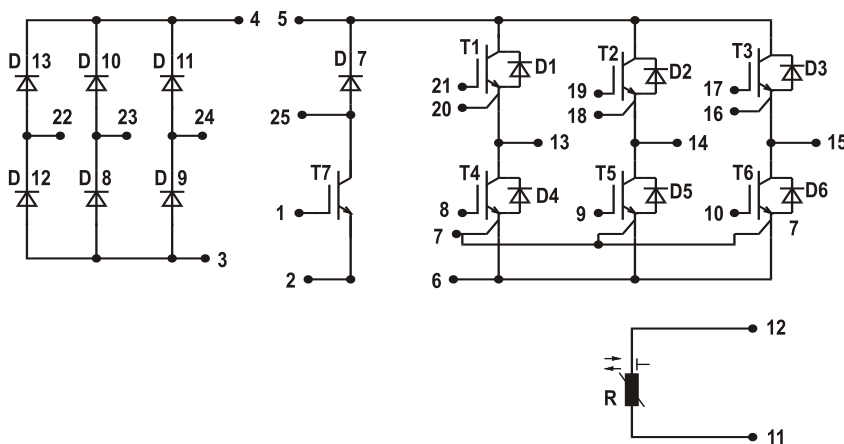
Converter - Brake - Inverter Module (CBI 1) NPT IGBT

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 600 \text{ V}$	$V_{CES} = 600 \text{ V}$
$I_{DAVM25} = 95 \text{ A}$	$I_{C25} = 12 \text{ A}$	$I_{C25} = 25 \text{ A}$
$I_{FSM} = 250 \text{ A}$	$V_{CE(sat)} = 2.25 \text{ V}$	$V_{CE(sat)} = 2.0 \text{ V}$

Preliminary data

Part name (Marking on product)

MUBW20-06A6K



E72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
 - low saturation voltage
 - positive temperature coefficient
 - fast switching
 - short tail current
- Epitaxial free wheeling diodes with hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Application:

- AC motor drives with
- Input from single or three phase grid
 - Three phase synchronous or asynchronous motor
 - Electric braking operation

Package:

- UL registered
- Industry standard E1-pack

Output Inverter T1 - T6

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{CES}	collector emitter voltage		$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			V
V_{GES}	max. DC gate voltage	continuous			± 20	V
V_{GEM}	max. transient collector gate voltage	transient			± 30	V
I_{C25}	collector current		$T_C = 25^{\circ}\text{C}$			A
I_{C80}			$T_C = 80^{\circ}\text{C}$			A
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			V
			$T_{VJ} = 125^{\circ}\text{C}$			V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.4\text{ mA}; V_{GE} = V_{CE}$	4.5		6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			mA
			$T_{VJ} = 125^{\circ}\text{C}$			mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			100	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		800		pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 15\text{ A}$		57		nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 15\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_{G(on)} = 39\ \Omega$ $R_{G(off)} = 22\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$			ns
t_r	current rise time		25		ns	
$t_{d(off)}$	turn-off delay time		160		ns	
t_f	current fall time		50		ns	
E_{on}	turn-on energy per pulse		0.42		mJ	
E_{off}	turn-off energy per pulse		0.44		mJ	
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 68\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$			A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 68\ \Omega;$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$			μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.5	K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)	0.55			K/W

Output Inverter D1 - D6

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 150^{\circ}\text{C}$			V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			A
I_{F80}			$T_C = 80^{\circ}\text{C}$			A
V_F	forward voltage	$I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			V
			$T_{VJ} = 125^{\circ}\text{C}$			V
I_{RM}	max. reverse recovery current	$V_R = 300\text{ V}$ $di_F/dt = -400\text{ A}/\mu\text{s}$ $I_F = 15\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 100^{\circ}\text{C}$			A
t_{rr}	reverse recovery time		14		ns	
$E_{rec(off)}$	reverse recovery energy		80		μJ	
			tbd			
R_{thJC}	thermal resistance junction to case	(per diode)			1.6	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)	0.55			K/W

$T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake Chopper T7

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{CES}	collector emitter voltage		$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			V	
V_{GES}	max. DC gate voltage	continuous			± 20	V	
V_{GEM}	max. transient collector gate voltage	transient			± 30	V	
I_{C25}	collector current		$T_C = 25^{\circ}\text{C}$			11	A
I_{C80}			$T_C = 80^{\circ}\text{C}$			8	A
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			50	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 10\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			2.65 3.1	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.2\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	4.5		6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			0.7	mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$				120	nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$				220	pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 300\text{ V}; V_{GE} = 15\text{ V}; I_C = 6\text{ A}$				32	nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 300\text{ V}; I_C = 8\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_{G(on)} = 54\ \Omega$ $R_{G(off)} = 22\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$			20	ns
t_r	current rise time					10	ns
$t_{d(off)}$	turn-off delay time					110	ns
t_f	current fall time					30	ns
E_{on}	turn-on energy per pulse					0.21	mJ
E_{off}	turn-off energy per pulse					0.26	mJ
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 54\ \Omega$ $L = 100\ \mu\text{H};$ clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$	$T_{VJ} = 125^{\circ}\text{C}$			18	A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 600\text{ V}; V_{GE} = \pm 15\text{ V};$ $R_G = 54\ \Omega;$ non-repetitive	$T_{VJ} = 125^{\circ}\text{C}$			10	μs
R_{thJC}	thermal resistance junction to case	(per IGBT)				2.75	K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)				0.9	K/W

Brake Chopper D7

Symbol	Definitions	Conditions	Ratings			Unit	
			min.	typ.	max.		
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 150^{\circ}\text{C}$			600	V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			21	A
I_{F80}			$T_C = 80^{\circ}\text{C}$			14	A
V_F	forward voltage	$I_F = 10\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			1.25	V V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			0.2	0.06 mA mA
I_{RM}	max. reverse recovery current	$V_R = 100\text{ V}; I_F = 12\text{ A}$ $di_F/dt = -100\text{ A}/\mu\text{s}$	$T_{VJ} = 100^{\circ}\text{C}$			3.5	A
t_{rr}	reverse recovery time					80	ns
R_{thJC}	thermal resistance junction to case	(per diode)				2.5	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)				0.85	K/W

$T_C = 25^{\circ}\text{C}$ unless otherwise stated

Input Rectifier Bridge D8 - D13

Symbol	Definitions	Conditions	Maximum Ratings	
V_{RRM}	max. repetitive reverse voltage		1600	V
I_{FAV}	average forward current	sine 180°	$T_C = 80^\circ\text{C}$	23 A
I_{DAVM}	max. average DC output current	rectangular; $d = 1/3$; bridge	$T_C = 80^\circ\text{C}$	65 A
I_{FSM}	max. surge forward current	$t = 10$ ms; sine 50 Hz	$T_C = 25^\circ\text{C}$	250 A
P_{tot}	total power dissipation		$T_C = 25^\circ\text{C}$	65 W

Symbol	Conditions	Characteristic Values				
		min.	typ.	max.		
V_F	forward voltage	$I_F = 30$ A	$T_{VJ} = 25^\circ\text{C}$	1.1	1.45	V
			$T_{VJ} = 125^\circ\text{C}$	1.2		V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.4	0.02	mA mA
R_{thJC}	thermal resistance junction to case	(per diode)	$T_{VJ} = 25^\circ\text{C}$		1.9	K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.65		K/W

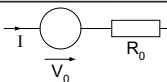
Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	
R_{25}	resistance		$T_C = 25^\circ\text{C}$	4.45	4.7	k Ω
$B_{25/85}$				3510	5.0	K

Module

Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		125	$^\circ\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^\circ\text{C}$
T_{stg}	storage temperature		-40		125	$^\circ\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1$ mA; 50/60 Hz			2500	V~
M_d	mounting torque	(M4)	2.0		2.2	Nm
d_S	creep distance on surface		12.7			mm
d_A	strike distance through air		12.7			mm
Weight				40		g

Equivalent Circuits for Simulation



Symbol	Definitions	Conditions	Ratings			
			min.	typ.	max.	
V_0	rectifier diode	D8 - D13	$T_{VJ} = 125^\circ\text{C}$	0.90		V
R_0				12		m Ω
V_0	IGBT	T1 - T6	$T_{VJ} = 125^\circ\text{C}$	1.0		V
R_0				70		m Ω
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^\circ\text{C}$	1.25		V
R_0				13		m Ω
V_0	IGBT	T7	$T_{VJ} = 125^\circ\text{C}$	1.4		V
R_0				150		m Ω
V_0	free wheeling diode	D7	$T_{VJ} = 125^\circ\text{C}$	1.25		V
R_0				26		m Ω

$T_C = 25^\circ\text{C}$ unless otherwise stated

